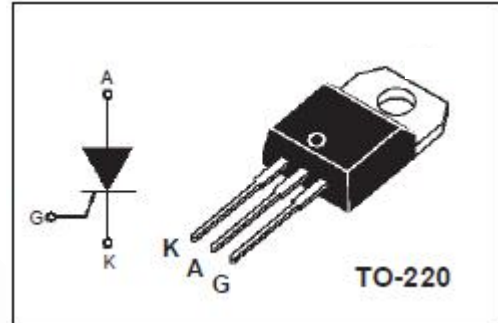


isc Thyristors
S6025L
DESCRIPTION

- With TO-220 packaging
- Electrically-isolated package
- High surge capability
- Glass passivated junctions and center gate fire for greater parameter uniformity and stability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


APPLICATIONS

- Switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER		MIN	UNIT
V _{DRM}	Repetitive peak off-state voltage		600	V
V _{RRM}	Repetitive peak reverse voltage		600	V
I _{T(RMS)}	RMS on-state current		25	A
I _{TSM}	Surge non-repetitive on-state current (1/2 cycle,sine wave;T _c =25°C)	50HZ 60HZ	300 350	A
P _{G(AV)}	Average gate power dissipation	T _p =8.3ms	0.5	W
T _j	Operating junction temperature		-40~125	°C
T _{stg}	Storage temperature		-40~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _{RM} =V _{RRM} V _{DM} =V _{DRM}	T _j =25°C		0.01	mA
I _{DRM}	Repetitive peak off-state current		T _j =100°C T _j =125°C		1.0 2.0	
V _{TM}	On-state voltage	I _{TM} = 25A			1.6	V
I _{GT}	Gate-trigger current	V _D = 12 V; R _L =60 Ω			35	mA
V _{GT}	Gate-trigger voltage	V _D = 12 V; R _L =60 Ω			1.5	V
R _{th(j-c)}	Thermal resistance	Junction to case			2.5	°C/W